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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Schottky Diode Gen²

 V_{RRM} = 150 V I_{FAV} = 2x 60 A V_{F} = 0.8 V

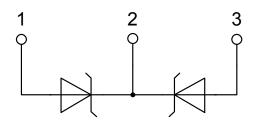
High Performance Schottky Diode Low Loss and Soft Recovery Common Cathode

Part number

DSA120C150QB



Backside: cathode



Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-3P

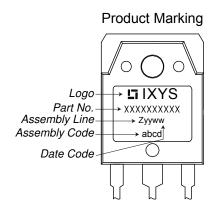
- Industry standard outline compatible with TO-247
- RoHS compliant
- Epoxy meets UL 94V-0



Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			150	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			150	V
I _R	reverse current, drain current	V _R = 150 V	$T_{VJ} = 25^{\circ}C$			900	μΑ
		$V_R = 150 V$	$T_{VJ} = 125^{\circ}C$			5	mΑ
V _F	forward voltage drop	I _F = 60 A	$T_{VJ} = 25^{\circ}C$			0.93	V
		$I_F = 120 \text{ A}$				1.13	V
		I _F = 60 A	T _{VJ} = 125°C			0.80	V
		$I_F = 120 \text{ A}$				1.03	V
I _{FAV}	average forward current	T _c = 150°C	T _{vJ} = 175°C			60	Α
		rectangular d = 0.5					i I I I
V _{F0}	threshold voltage $T_{VJ} = 175$		T _{vJ} = 175°C			0.51	V
r _F	slope resistance	oss calculation only				3.9	mΩ
R _{thJC}	thermal resistance junction to case				0.4	K/W	
R _{thCH}	thermal resistance case to heatsing	nk			0.25		K/W
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			375	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			1.20	kA
CJ	junction capacitance	V _R = 24 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		481		pF



Package	e TO-3P			Ratings	3	
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal 1)			70	Α
T _{VJ}	virtual junction temperature		-55		175	°C
T _{op}	operation temperature		-55		150	°C
T _{stg}	storage temperature		-55		150	°C
Weight				5		g
M _D	mounting torque		0.8		1.2	Nm
F _c	mounting force with clip		20		120	N



Part number

D = Diode

S = Schottky Diode

A = low VF

120 = Current Rating [A] C = Common Cathode

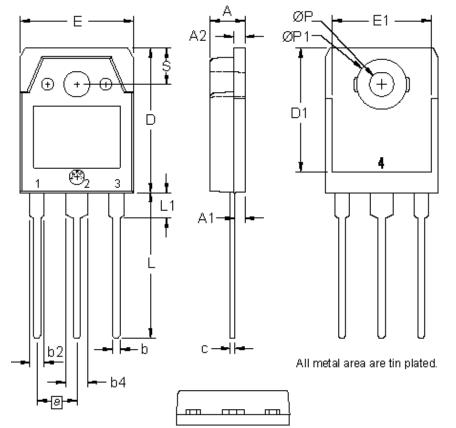
150 = Reverse Voltage [V] QB = TO-3P (3)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA120C150QB	DSA120C150QB	Tube	30	501788

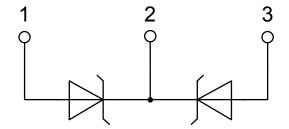
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 175 ^{\circ}C$
$I \rightarrow V_0$	R_0	Schottky		
V _{0 max}	threshold voltage	0.51		V
R _{0 max}	slope resistance *	1.3		mΩ



Outlines TO-3P



Dim.	Millimeter		Inches		
DIIII.	min	max	min	max	
Α	4.70	4.90	0.185	0.193	
A1	1.30	1.50	0.051	0.059	
A2	1.45	1.65	0.057	0.065	
b	0.90	1.15	0.035	0.045	
b2	1.90	2.20	0.075	0.087	
b4	2.90	3.20	0.114	0.126	
С	0.55	0.80	0.022	0.031	
D	19.80	20.10	0.780	0.791	
D1	16.90	17.20	0.665	0.677	
Е	15.50	15.80	0.610	0.622	
E1	13.50	13.70	0.531	0.539	
е	5.45 BSC		0.215	BSC	
L	19.80	20.20	0.780	0.795	
L1	3.40	3.60	0.134	0.142	
ØР	3.20	3.40	0.126	0.134	
ØP1	6.90	7.10	0.272	0.280	
S	4.90	5.10	0.193	0.201	





Schottky

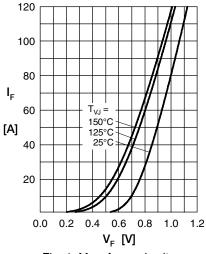


Fig. 1 Max. forward voltage drop characteristics

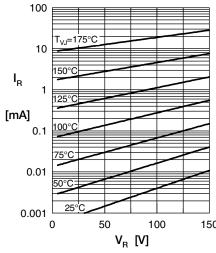


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

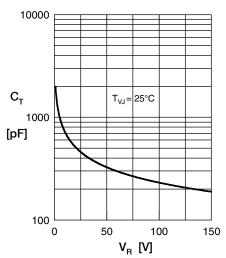


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

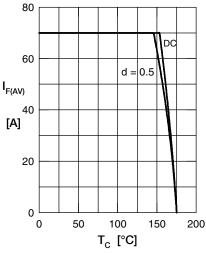


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp T_C

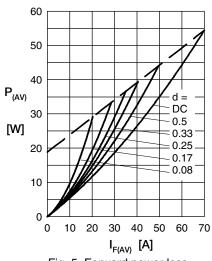


Fig. 5 Forward power loss characteristics

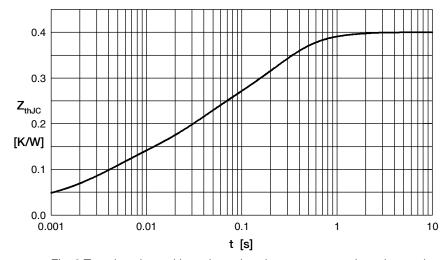


Fig. 6 Transient thermal impedance junction to case at various duty cycles

R_{thi}	t _i
0.022	0.0002
0.082	0.0032
0.104	0.026
0.165	0.208

0.027 0.79

Note: All curves are per diode